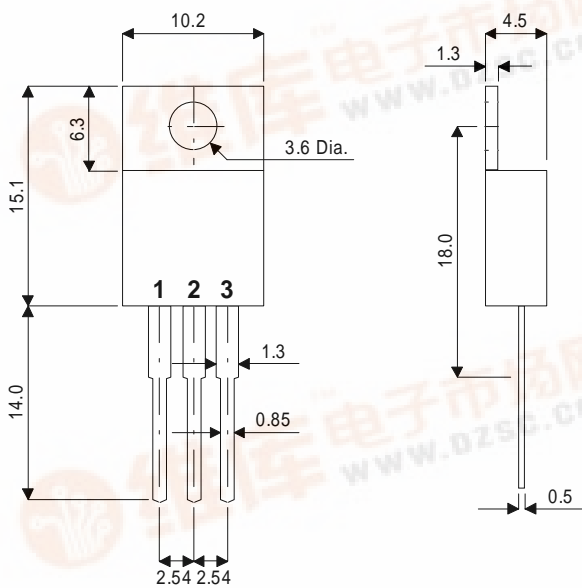




BUL57A

MECHANICAL DATA

Dimensions in mm



TO220

Pin 1 – Base Pin 2 – Collector Pin 3 – Emitter

**ADVANCED
DISTRIBUTED BASE DESIGN
HIGH VOLTAGE
HIGH SPEED NPN
SILICON POWER TRANSISTOR**

Designed for use in
electronic ballast applications

- SEMEFAB DESIGNED AND DIFFUSED DIE
- HIGH VOLTAGE
- FAST SWITCHING
- HIGH ENERGY RATING

FEATURES

- Multi-base for efficient energy distribution across the chip resulting in significantly improved switching and energy ratings across full temperature range.
- Ion implant and high accuracy masking for tight control of characteristics from batch to batch.
- Triple Guard Rings for improved control of high voltages.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage ($I_E = 0$)	200V
V_{CEO}	Collector – Emitter Voltage ($I_B = 0$)	70V
V_{EBO}	Emitter – Base Voltage ($I_C = 0$)	10V
I_C	Continuous Collector Current	22A
$I_{C(PK)}$	Peak Collector Current	32A
	Base Current	6A
	Total Dissipation at $T_{case} = 25^{\circ}C$	80W
	Operating and Storage Temperature Range	-55 to +150°C



ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit			
ELECTRICAL CHARACTERISTICS								
$V_{CEO(sus)}$	Collector – Emitter Sustaining Voltage	$I_C = 10mA$	70					
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 1mA$	200		V			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	$I_E = 1mA$	10					
I_{CBO}	Collector – Base Cut-Off Current	$V_{CB} = 200V$			10			
			$T_C = 125^{\circ}C$		100	μA		
I_{CEO}	Collector – Emitter Cut-Off Current	$I_B = 0$	$V_{CE} = 60V$		100			
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 9V$	$I_C = 0$	$T_C = 125^{\circ}C$	10			
					100	μA		
h_{FE}^*	DC Current Gain	$I_C = 0.3A$	$V_{CE} = 4V$	30	90			
				$I_C = 5A$	$V_{CE} = 4V$	25	60	
				$I_C = 15A$	$V_{CE} = 4V$	20	50	
			$T_C = 125^{\circ}C$					
$V_{CE(sat)}^*$	Collector – Emitter Saturation Voltage	$I_C = 1A$	$I_B = 0.1A$		0.1	0.2		
				$I_C = 5A$	$I_B = 0.5A$		0.3	0.6
				$I_C = 15A$	$I_B = 1.5A$		1.0	1.5
$V_{BE(sat)}^*$	Base – Emitter Saturation Voltage	$I_C = 5A$	$I_B = 0.5A$			1.2		
				$I_C = 15A$	$I_B = 1.5A$			1.4
DYNAMIC CHARACTERISTICS								
f_t	Transition Frequency	$I_C = 0.2A$	$V_{CE} = 4V$		20	MHz		
C_{ob}	Output Capacitance	$V_{CB} = 10V$	$f = 1MHz$			pF		

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$